

Resume

Basic Information

Name : HIMANSHU TEWARI
Course : PG - DIoT, Feb19
Address : S/o Harish Chandra Tewari, House No.26, Vikasnagar,
Bithoriya No.1, Kusumkhera, Haldwani, Uttarakhand

CCPP ID : PI0010



PG - DIoT Marks

S.NO.	Module	Maximum Marks (Theory)	Obtained Marks
1	Fundamentals of IoT and Mobile & Web Applications	40	20
2	Programming Technologies	40	31
3	Microcontrollers Programming	40	27
4	Embedded Linux Platforms	40	22
5	Network Programming & Wireless Technologies	40	27
6	Data Management & Analytics	40	22
7	Edge Computing & Protocols	40	22
8	Cloud Computing	40	17
9	Technological Aggregation & Case Studies	40	28
	Total	360	216

Academic Details

Level	Stream	Institute	Board/University	Passing Year	Degree %	Division
BTech	Electronics & Communication	G B Pant Engineering College, Pauri Garhwal, Uttarakhand	Uttarakhand Technical University, Dehradun, Uttarakhand	2013	67.24 %	I
Polytechnic	Electronics	Government Polytechnic Shaktifarm, US Nagar, Uttarakhand	Uttarakhand Board of Technical Education, Roorkee, Uttarakhand	2009	66.19 %	I
X	General	Little Scholars	CBSE	2006	53.8 %	II

Academic Projects

Title	: IoT Based Solutions for Smart Farming	Duration : 1 Month
Platform	: Python, NodeJS, Express, InfluxDB, Docker	
Description	: The proposed system is designed for automatic irrigation & real-time monitoring of soil moisture, humidity and crop diseases. It consists of Raspberry Pi & camera, Esp32/8266, soil and DHT11 sensor, servo motor & a water pump. It includes various cases of crops based on crop image analysis. From captured images, parameters that are planned for analysis are, amount of green leaf detection and moisture content in soil. Thus proposed system will improve the productivity & benefit irrigation sector	
Title	: Vertical Scaling of In _{0.7} Ga _{0.3} As HEMTs for POST-Si-CMOS Logic Applications	Duration : 6 Months
Platform	: VLSI Design	
Description	: The work presented in this thesis is divided into two steps, namely (1) Verification of simulator performance by simulating a reported device and comparing the simulation results with the experimental results (2) Vertical Scaling of InGaAs HEMT and comparison of characteristics at t _{ins} =6.5nm and 3nm. Various design parameters of InGaAs are discussed before starting simulation.	

Other Information

Extra Curricular : Lead my college team in University Level Badminton Chamoionship(Ranked 2nd). College Badminton Coordinator

Personal Information

Date of Birth : 09/02/1990

Gender : Male

Nationality : Indian

Languages Known : Hindi, English

I hereby declare that the information given above is true to the best of my Information knowledge belief.

Date :

Signature :

P_DI_08